

600V N-Channel Super Junction MOSFET

Voltage	600 V	Rdson	74 mΩ
Current	53 A	Qg	84 nC

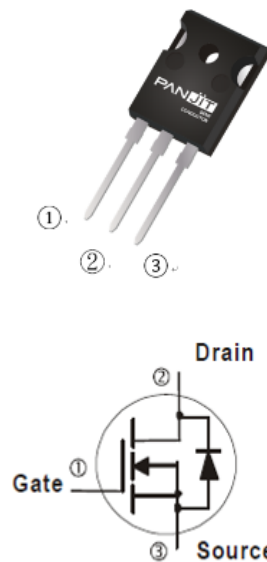
Feature:

- $R_{DS(ON)}$ Max, $V_{GS}@10V$: 74mΩ
- Fast recovery Q_{rr} / T_{rr} performance.
- High Speed Switching and Low $R_{DS(ON)}$
- 100% Avalanche Tested
- 100% Rg Tested
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: TO-247AD-3LD package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 6.231 grams

TO-247AD-3LD



Application

- PFC, TV Power, PC Power, PD Charger, Adapter, UPS

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage @ T_{jmax}		V_{DS}	650	V
Drain-Source Voltage		V_{DS}	600	
Gate-Source Voltage		V_{GS}	± 30	
Continuous Drain Current	$T_C=25^\circ\text{C}$	I_D	53	A
	$T_C=100^\circ\text{C}$		33	
Pulsed Drain Current	$T_C=25^\circ\text{C}$	I_{DM}	117	A
Single Pulse Avalanche Energy		E_{AS}	1750	mJ
MOSFET dv/dt ruggedness		dv/dt	100	V/ns
Power Dissipation	$T_C=25^\circ\text{C}$	P_D	446	W
	$T_C=100^\circ\text{C}$		178	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	$^\circ\text{C}$

Thermal Characteristics

PARAMETER		SYMBOL	MAXIMUM	UNITS
Thermal Resistance	Junction-to-Case	$R_{\theta JC}$	0.3	$^\circ\text{C/W}$
	Junction-to-Ambient (Note 3)	$R_{\theta JA}$	50	$^\circ\text{C/W}$

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=1mA$	600	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	3.5	4.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=26.5A^{(Note1)}$	-	63	74	m Ω
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=600V, V_{GS}=0V$	-	-	10	μA
Gate-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 30V, V_{DS}=0V$	-	-	± 100	nA
Transfer characteristics	gfs	$V_{DS}=20V, I_D=26.5A$	-	27	-	S
Dynamic (Note 5)						
Total Gate Charge	Q_g	$V_{DS}=480V, I_D=26.5A,$ $V_{GS}=10V$	-	84	-	nC
Gate-Source Charge	Q_{gs}		-	21	-	
Gate-Drain Charge	Q_{gd}		-	33	-	
Input Capacitance	C_{iss}	$V_{DS}=400V, V_{GS}=0V,$ $f=250kHz$	-	3871	-	pF
Output Capacitance	C_{oss}		-	108	-	
Reverse Transfer Capacitance	C_{rss}		-	7.5	-	
Effective Output Capacitance Energy Related	$C_{o(er)}$	$V_{DS}=0V$ to 400V, $V_{GS}=0V, f=250kHz$ (Note 4)	-	160	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V, I_D=26.5A,$ $V_{GS}=10V, R_G=25\Omega$ (Note 2)	-	70	-	ns
Turn-On Rise Time	t_r		-	96	-	
Turn-Off Delay Time	$t_{d(off)}$		-	237	-	
Turn-Off Fall Time	t_f		-	90	-	
Gate Resistance	R_g	$f=1.0MHz$	-	0.7	-	Ω
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S		-	-	53	A
Diode Forward Voltage	V_{SD}	$I_S=26.5A, V_{GS}=0V$	-	0.9	1.5	V
Reverse Recovery Charge	Q_{rr}	$I_S=26.5A$	-	1.0	-	μC
Reverse Recovery Time	T_{rr}	$di/dt=100A/\mu s$	-	150	-	ns

NOTES :

1. Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance.
4. $C_{o(er)}$ is a capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0V to 80% $V_{(BR)DSS}$
5. Guaranteed by design, not subject to production testing

TYPICAL CHARACTERISTIC CURVES

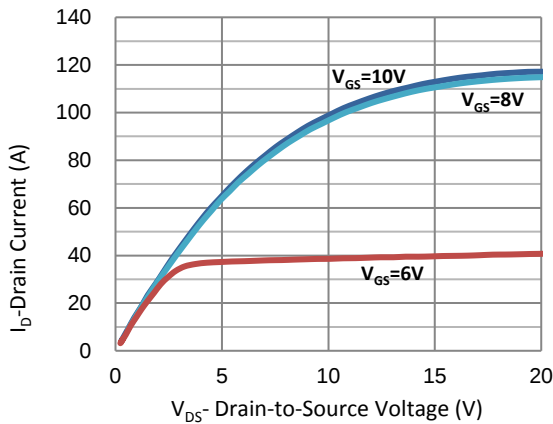


Fig.1 Output Characteristics

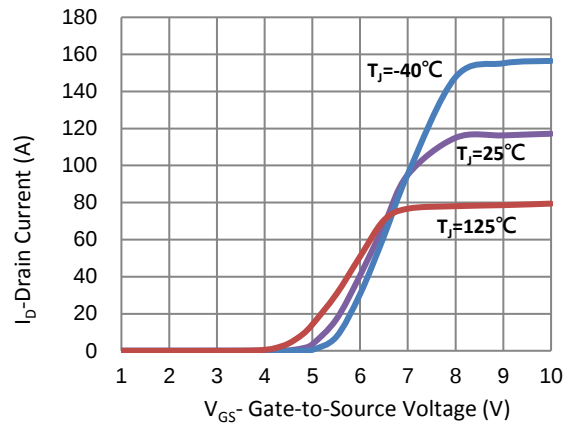


Fig.2 Transfer Characteristics

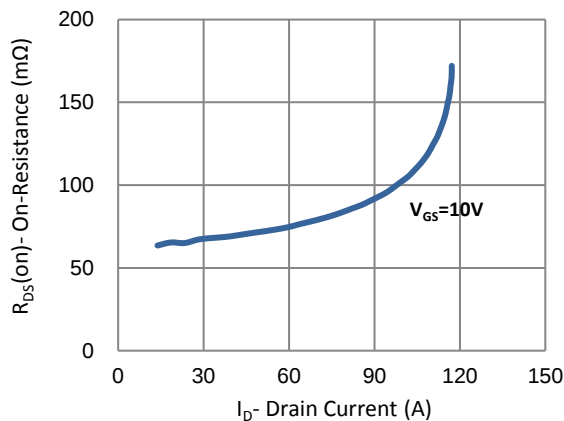


Fig.3 On-Resistance vs. Drain Current

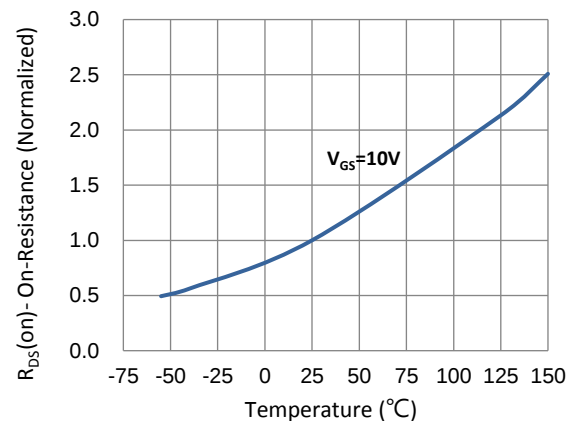


Fig.4 On-Resistance vs. Junction Temperature

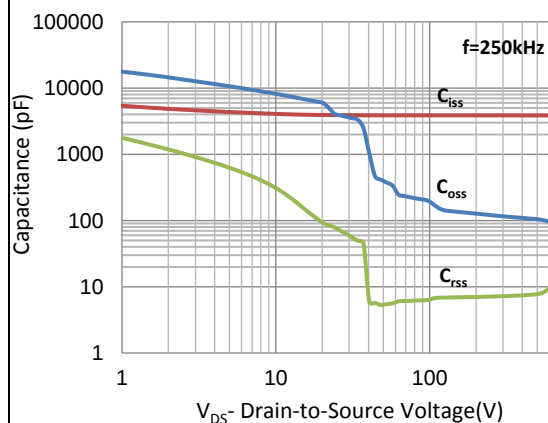


Fig.5 Capacitance vs. Drain-Source Voltage

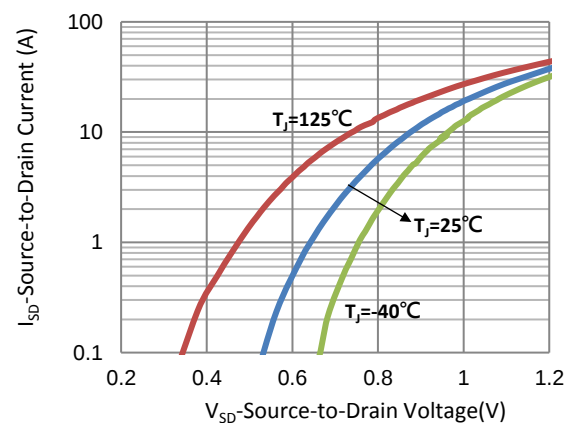


Fig.6 Source-Drain Diode Forward Voltage

TYPICAL CHARACTERISTIC CURVES

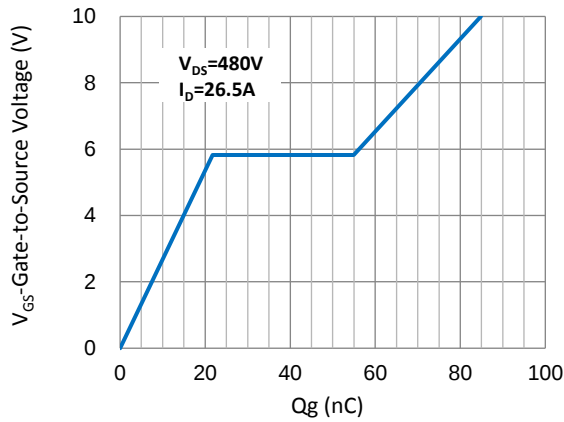


Fig.7 Gate-Charge Characteristics

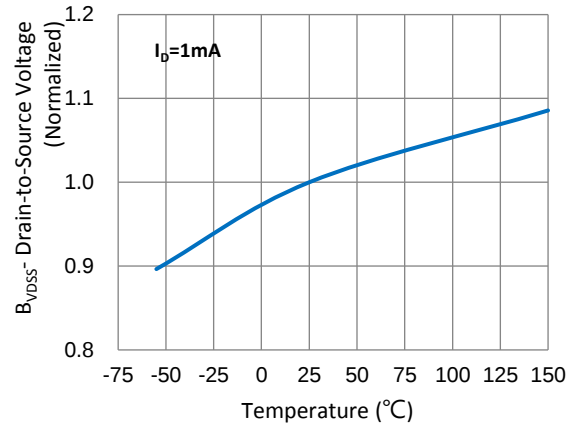


Fig.8 Breakdown Voltage Variation vs. Temperature

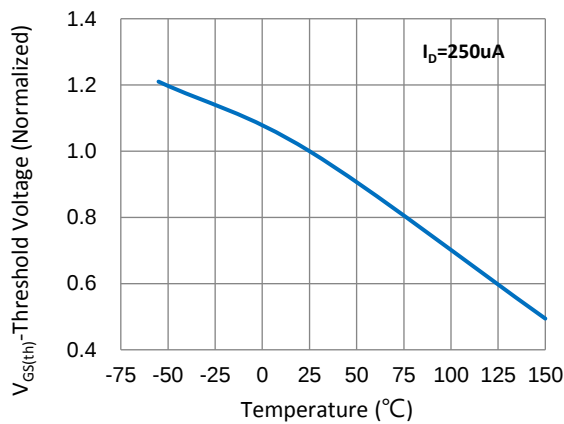


Fig.9 Threshold Voltage Variation with Temperature

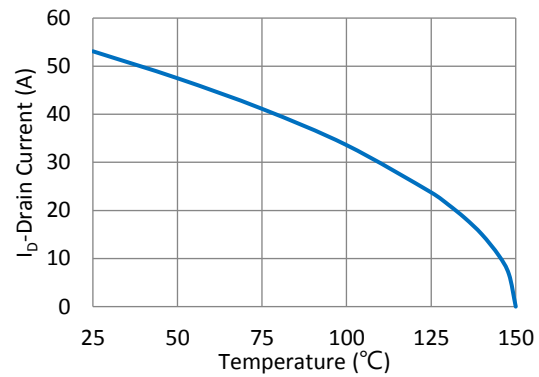


Fig.10 Drain Current vs. Case Temperature

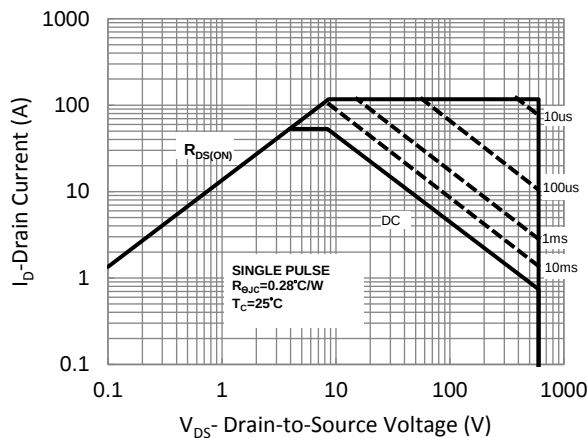


Fig.11 Maximum Safe Operating Area

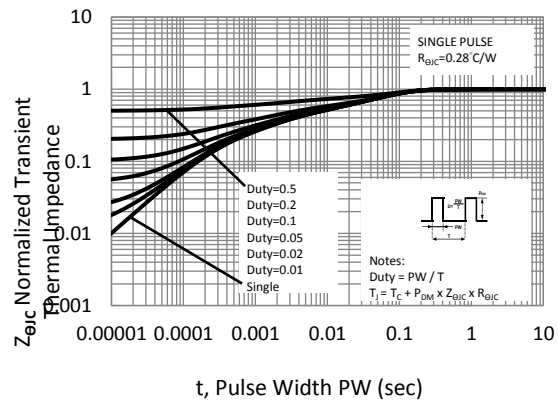


Fig.12 Normalized Transient Thermal Impedance

TYPICAL CHARACTERISTIC CURVES

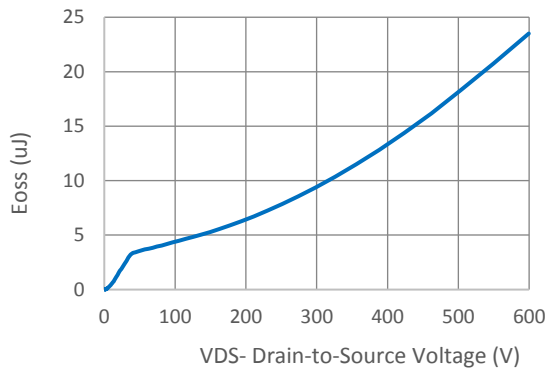
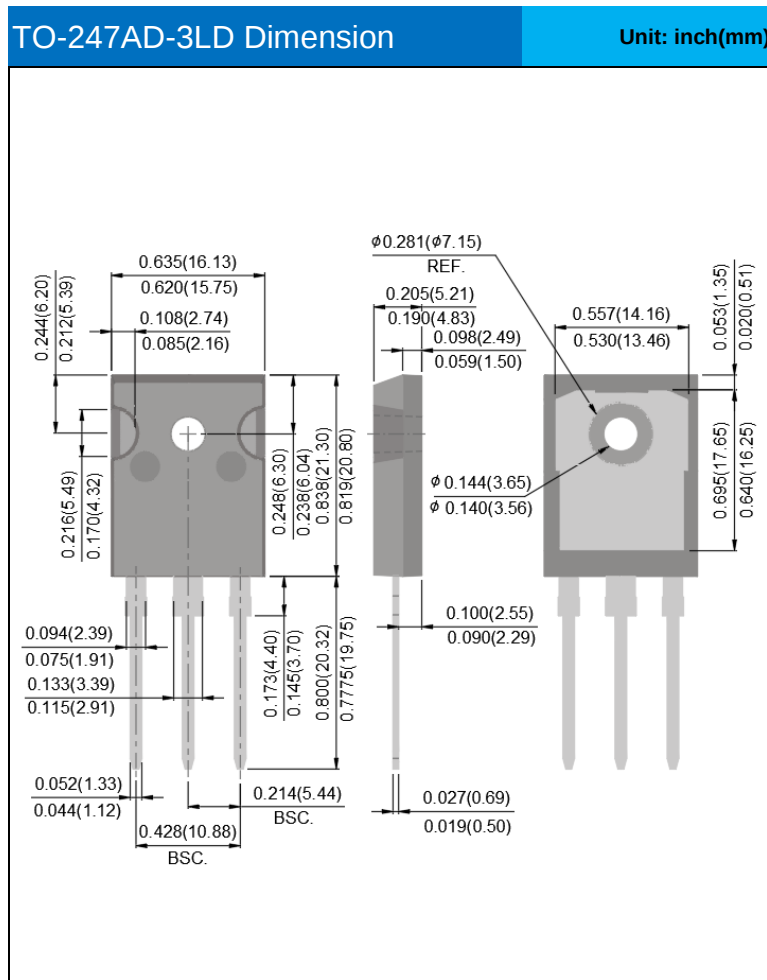


Fig.13 Typ. Coss Stored Energy

Product and Packing Information

Part No.	Package Type	Packing Type	Marking
PJMH074N60FRC	TO-247AD-3LD	30pcs / Tube	074N60FRC

Packaging Information



Marking Diagram

PJ	Y = Year Code
074N60FRC	W = Week Code (A~Z)
YWLL x	LL = Lot Code (00~99)
	x = Production Line Code

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